PATENT ABSTRACTS OF JAPAN

(11)Publication number :　　　64-081236

(43)Date of publication　f application : 27.03.1989

| (51)Int.Cl. | HO1L 21/60 |
| | HO1L 21/88 |

| (21)Application number : 62-237156 | (71)Applicant : HITACHI LTD |
| (22)Date of filing :　　　24.09.1987 | (72)Inventor : ITO TOMOYASU |

(54) SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

(57)Abstract:

PURPOSE: To improve humidity resistance by decreasing the number of insulation films between layers below bonding pad by forming bonding pad at the conductive film below conductive layer at the uppermost layer or by partially eliminating the insulation film below bonding pad consisting of conductive film at the uppermost layer.
CONSTITUTION: Bonding pad PAD is constituted, for example, by aluminum film of the first layer which is the same as that of a wiring 5 and insulation films 6, 8, and 10 on the PAD are opened (11) each to allow the bonding pad PAD to be exposed or it is formed by the aluminum film of the uppermost layer (third layer) which is the same as that of a wiring 9 to allow an insulation film between layers 8 of the third layer and an insulation film between films 6 of the second layer to be eliminated. In either case, only an insulation film between layers 4 of the first layer is placed between itself and a field insulation film 3 and various kinds of insulation films of different property are not provided. It gives strength against shock applied on wire bonding and prevents crack to be formed on the insulation film 4.
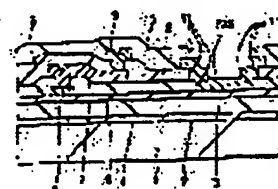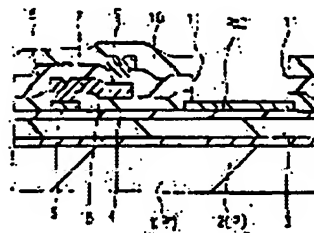
LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]